# AIDW16S65C5

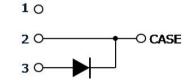


650V/16A Silicon Carbide Schottky Diode in TO247-3

### Features

- Revolutionary semiconductor material Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Junction Temperature range from -40°C to 175°C
- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI





RoHS

Infineon

### **Potential Applications**

- Traction inverter
- Booster / DCDC Converter
- On board Charger / PFC

## **Product Validation**

"Qualified for Automotive Applications. Product Validation according to AEC-Q100/101"

## Description

The 5th Generation CoolSiC<sup>™</sup> Automotive Schottky Diode represents Infineon leading edge technology for Silicon Carbide Schottky Barrier diodes. Thanks to a compact design and a technology based on thin wafers, this family of products shows improved efficiency over all load conditions resulting from both its thermal characteristics and low figure of merit (Qc x Vf). This product family has been designed to complement Infineon's IGBT and CoolMOS<sup>™</sup> portfolio. This ensures meeting the most stringent application requirements in the 650V voltage class.

Green

Product Information				
Ordering Code	AIDW16S65C5			
Marking	AD1665C5			
Package	PG-TO247-3-41			
SP Number	SP001725218			

Parameter	Value/Unit			
V <sub>DC,max</sub>	650 V			
I <sub>F</sub> ; T <sub>C</sub> < 129 °C	16 A			
$Q_{\rm C}; V_{\rm R}$ = 400 V	23 nC			
E <sub>C</sub> ; V <sub>R</sub> = 400 V	5.4 μJ			
T <sub>j,max</sub>	175 °C			

Pin Definition	
Pin 2, case	Cathode
Pin 3	Anode



Table of Contents

# **Table of Contents**

Featu	ires	1
Poter	ntial Applications	1
Produ	uct Validation	1
Descr	iption	1
Table	of Contents	2
1	Maximum Ratings	3
2	Thermal Characteristics	4
3	Electrical Characteristics	5
4	Electrical Characteristics Diagrams	6
5	Package Outlines	9
Revis	ion History	10



Maximum Ratings

# 1 Maximum Ratings

Table 1Maximum ratings1

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>	650	V
Continuous forward current for $R_{thJC,max}$ T <sub>c</sub> = 129 °C, D=1	I <sub>F</sub>	16	А
Surge non-repetitive forward current, sine halfwave $T_c=25$ °C, $t_p=10$ ms $T_c=150$ °C, $t_p=10$ ms	I <sub>F,SM</sub>	95 74	A
Non-repetitive peak forward current T <sub>c</sub> = 25°C, t <sub>p</sub> =10µs	l <sub>F,max</sub>	637	А
$i^{2}t$ value T <sub>c</sub> = 25°C, t <sub>p</sub> =10ms T <sub>c</sub> = 150°C, t <sub>p</sub> =10ms	∫i <sup>2</sup> dt	45 28	A <sup>2</sup> s
Diode dv/dt ruggedness V <sub>R</sub> =0480V	dv/dt	100	V/ns
Power dissipation T <sub>c</sub> = 25°C	P <sub>tot</sub>	94	W
Operating temperature	Т <sub>ј</sub>	-40175	°C
Storage temperature	T <sub>stg</sub>	-55150	°C
ESD Human body model, R= 1.5 kΩ, C = 100 pF Charged device model		8 2	kV
Soldering temperature, wavesoldering only allowed at leads, 1.6mm (0.063 in.) from case for 10 s	T <sub>sold</sub>	260	°C
Mounting Torque (M3 and M4 screws)		70	Ncm



**Thermal Characteristics** 

# 2 Thermal Characteristics

Table 2Thermal Characteristics1

Darameter	Symbol	Values			110:4	Noto /Toot oon dition
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
Thermal resistance, junction–case <sup>2</sup>	$R_{thJC}$	-	1.2	1.6	K/W	
Thermal resistance, junction-ambient <sup>2</sup>	$R_{thJA}$	-	-	62	K/W	



**Electrical Characteristics** 

# 3 Electrical Characteristics

#### Table 3Static Characteristics

Deremeter	Symbol	Values			Unit	Noto /Toot oon didion
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
DC blocking voltage	V <sub>DC</sub>	650	-	-		T <sub>j</sub> = 25°C, I <sub>R</sub> = 0.09 mA
Diode forward voltage <sup>3</sup>	V <sub>F</sub>	-	1.5	1.7	v	T <sub>j</sub> = 25°C, I <sub>F</sub> = 16 A
		-	1.8	2.1		T <sub>j</sub> = 150°C, I <sub>F</sub> = 16 A
Reverse current	I <sub>R</sub>	-	3	90		V <sub>R</sub> = 650 V, T <sub>j</sub> = 25 °C
		-	19	-	μA	V <sub>R</sub> = 650 V, T <sub>j</sub> = 150 °C

### Table 4Dynamic Characteristics at Tj=25°C unless noted otherwise

Parameter	Symbol	Values			Unit	Noto/Test condition
Falametei		Min.	Тур.	Max.	Unit	Note/Test condition
Total capacitive charge	Qc	-	23	-	nC	$V_R = 400 V, di/dt = 200 A/\mu s,$ $I_F \le I_{F,MAX}, T_j = 150 °C$
Total capacitance	С	-	471	-	pF	V <sub>R</sub> = 1 V, f = 1 MHz
		-	61	-		V <sub>R</sub> = 300 V, f= 1 MHz
		-	60	-		V <sub>R</sub> = 600 V, f= 1 MHz

#### Footnotes:

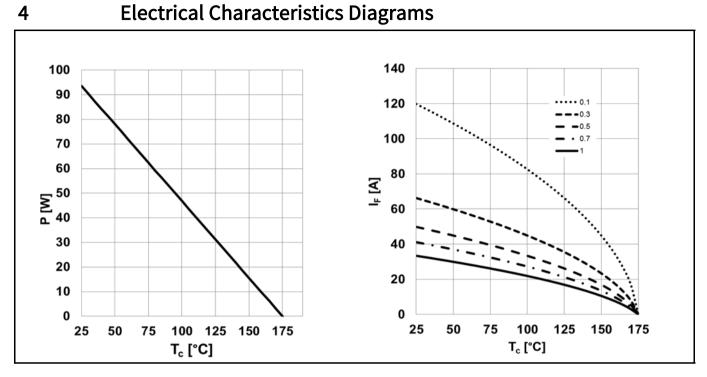
<sup>1</sup> The parameter is not subject to production test- verified by design/characterization.

<sup>2</sup> Rth,JC defined as per JESD-51-14. Rth,JA defined as per JESD-51-2.

<sup>3</sup> Only the value at 25°C is subject to production test. The value at 150°C is only verified by design/characterization.

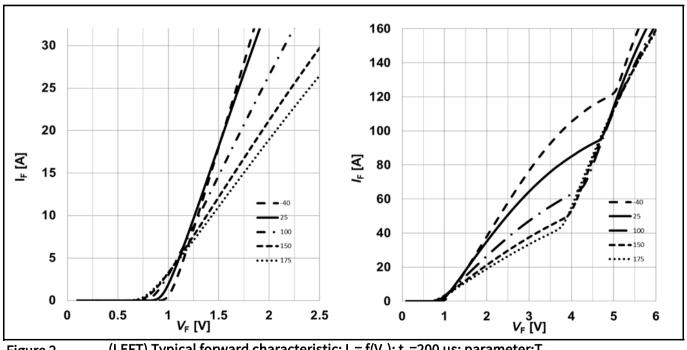


**Electrical Characteristics Diagrams** 





(LEFT) Power dissipation;  $P_{tot} = f(T_C)$ ;  $R_{thJC,max}$ (RIGHT) Diode forward current;  $I_F = f(T_C)$ ;  $T_j \le 175$  °C;  $R_{thJC,max}$ ; parameter: D=duty cycle





(LEFT) Typical forward characteristic; I<sub>F</sub>= f(V<sub>F</sub>); t<sub>P</sub>=200 μs; parameter:T<sub>j</sub> (RIGHT) Typical forward characteristics in surge current; I<sub>F</sub>= f(V<sub>F</sub>); t<sub>P</sub>=200 μs; parameter:T<sub>j</sub>



### **Electrical Characteristics Diagrams**

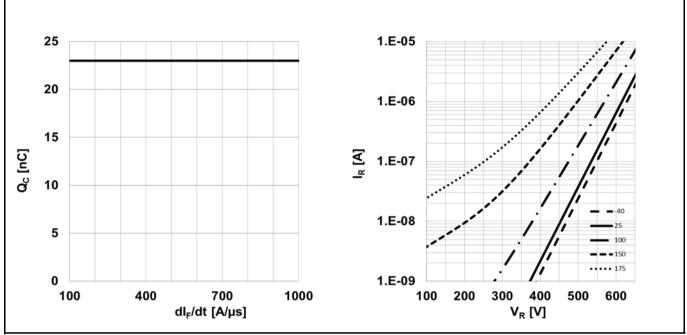
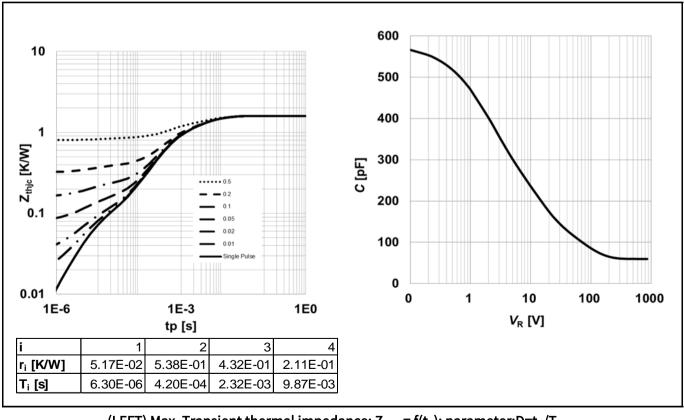


Figure 3(LEFT) Typical capacitive charge versus current slope (only capacitive charge, guaranteed<br/>by design);  $Q_c = f(di_F/dt)$ ;  $T_j = 150^{\circ}C$ ;  $V_R = 400V$ ;  $I_F \le I_{F,max}$ <br/>(RIGHT) Typical reverse current versus reverse voltage;  $I_R = f(V_R)$ ; parameter:  $T_i$ 





(LEFT) Max. Transient thermal impedance;  $Z_{thJC} = f(t_P)$ ; parameter:D= $t_P/T$  (RIGHT) Typ. Capacitance vs. Reverse voltage; C=  $f(V_R)$ ;  $T_i = 25^{\circ}$ C; f=1 MHz



### **Electrical Characteristics Diagrams**

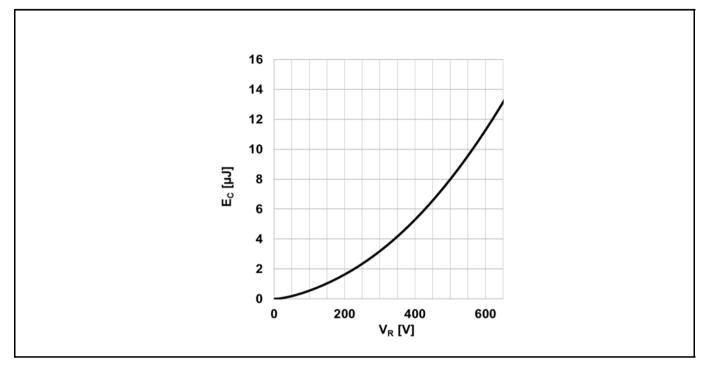
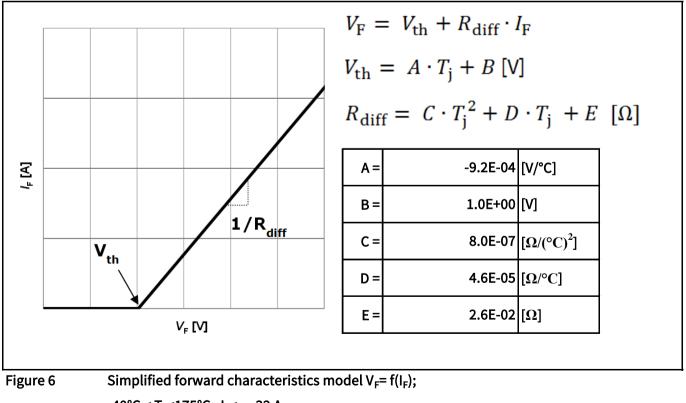


Figure 5 Typical capacitance stored energy;  $E_c = f(V_R)$ 



-40°C <  $T_j$  <175°C;  $I_F$  32 A



#### Package Outlines

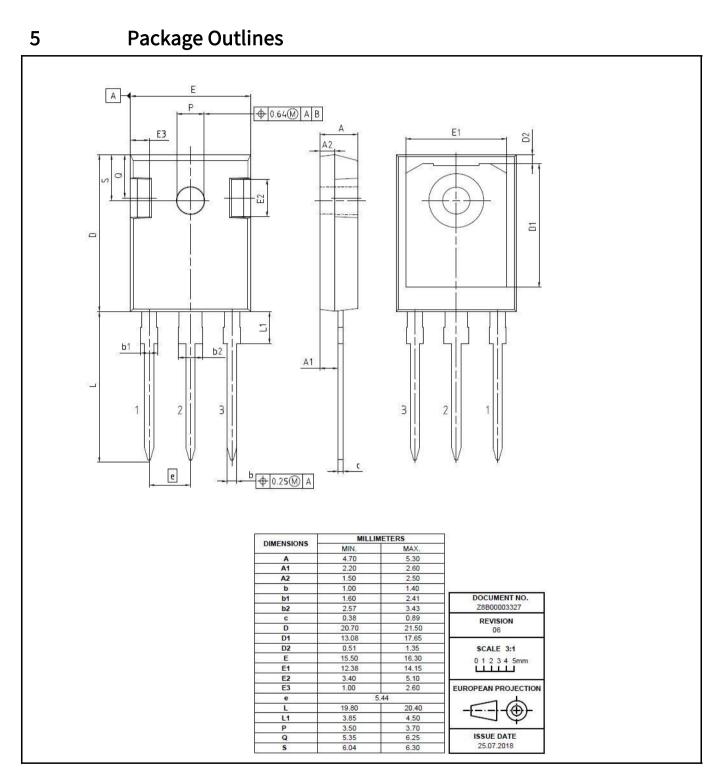


Figure 6

Package outline of PG-TO247-3-41 leaded (Dimensions in mm)



### **Revision History**

# **Revision History**

Document Version	Date of Release	Description of changes			
V3.0	26.11.2018	1st release of Data Sheet			



#### Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

	IMPORTANT NOTICE
Edition 2017-07-07	
	The information given in this document shall in no event For further information on the product,
Published by	be regarded as a guarantee of conditions or characteristics technology, delivery terms and conditions and
Infineon Technologies AG	("Beschaffenheitsgarantie"). prices please contact your nearest Infineon
81726 München, Germany	Technologies office (www.infineon.com).
	With respect to any examples, hints or any typical values
© 2017 Infineon Technologies AG.	stated herein and/or any information regarding the WARNINGS
All Rights Reserved.	application of the product, Infineon Technologies hereby Due to technical requirements products may
	disclaims any and all warranties and liabilities of any kind, contain dangerous substances. For information
Do you have a question about this	including without limitation warranties of non- on the types in question please contact your
document?	infringement of intellectual property rights of any third nearest Infineon Technologies office.
Email: erratum@infineon.com	party.
Document reference	In addition, any information given in this document is Except as otherwise explicitly approved by subject to customer's compliance with its obligations Infineon Technologies in a written document stated in this document and any applicable legal signed by authorized representatives of Infineon requirements, norms and standards concerning Technologies, Infineon Technologies' products customer's products and any use of the product of may not be used in any applications where a Infineon Technologies in customer's applications. failure of the product or any consequences of the use thereof can reasonably be expected to
	The data contained in this document is exclusively result in personal injury. intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon(英飞凌)